

DESCRIPTION

The IS341W Photocoupler is ideally suited for driving power IGBTs and MOSFETs used in inverters of motor control and of power supply system. It contains an AIGaAs LED optically coupled to an integrated circuit with a power output stage. The high peak output current of 3.0A is capable to direct drive IGBT with ratings up to 1200 V/100 A. For IGBTs with higher ratings, IS341W can be used to drive a discrete power stage which drives the IGBT gate.

The device is supplied in Stretched SO6 package with wide lead separation.

FEATURES

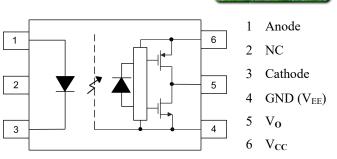
- 3.0A Maximum Peak Output Current
- Rail-to-Rail Output Voltage
- 35kV/µs Minimum Common Mode Rejection at V_{CM} 1500V
- Maximum Propagation Delay 200ns
- Maximum Propagation Delay Difference 100ns
- Wide Operating Voltage Range
- V_{cc} 15 to 30 V
- Under Voltage Lock Out (UVLO) Protection with Hysteresis
- Guaranteed Performance over Temperature Range -40°C to +125°C
- MSL Level 1
- RoHS Compliant
- UL E91231 Model "I341"

APPLICATIONS

- IGBT/MOSFET Gate Drive
- UPS
- Industrial Inverters
- Switching Power Supplies
- AC and Brushless DC Motor Drives

ORDER INFORMATION

Supplied in Tape & Reel



A 0.1µF bypass Capacitor must be connected between Pins 6 and 4.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Stresses exceeding the absolute maximum ratings can cause permanent damage to the device.

Exposure to absolute maximum ratings for long periods of time can adversely affect reliability.

Input

25mA
1.0A
5V
500ns
125°C
45mW
3.0A
3.0A
35V
V _{CC}
125°C
700mW
$5000V_{\text{RMS}}$
745mW
−40 to 125°C
−55 to 150°C
260°C

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Truth Table

LED	V _{cc} – GND (Turn ON, +ve going)	V _{cc} – GND (Turn OFF –ve going)	Vo
OFF	0 – 30V	0-30V	LOW
ON	0-11.0V	0-9.5V	LOW
ON	11.0 - 13.5V	9.5 – 12.0V	TRANSITION
ON	13.5 – 30V	12 – 30V	HIGH

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-40	125	°C
Supply Voltage	$V_{CC} - V_{EE}$	15	30	V
Input Current (ON)	I _{F(ON)}	8	16	mA
Input Voltage (OFF)	V _{F(OFF)}	-3.0	0.8	V
Operating Frequency	f		75	kHz

Notes :

Input Current (ON) : Rise and Fall times should be less than 500ns

 I_{OPH} : Exponential Waveform \geq -3.0A (\leq 0.3 µs), T_A = 125°C

 I_{OPL} : Exponential Waveform $\leq 3.0A~(\leq 0.3~\mu s),\,T_A$ = 125°C



ELECTRICAL CHARACTERISTICS (Typical Values at V_{CC} – V_{EE} = 30V and T_A = 25°C, Minimum and Maximum Values at Recommended Operating Conditions, unless otherwise specified)

INPUT

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward Voltage	V_{F}	$I_F = 10 mA$	1.2	1.37	1.8	V
Forward Voltage Temperature Coefficient	$\Delta V_F / \Delta T$	$I_F = 10 mA$		-2.0		mV/°C
Reverse Voltage	V _R	$I_R = 10 \mu A$	5			V
Input Threshold Current (Low to High)	I _{FLH}	$V_{CC} = 30V$ $V_O > 5V$		2.5	5	mA
Input Threshold Voltage (High to Low)	V_{FHL}	$V_{CC} = 30V$ $V_O < 5V$	0.8			V
Input Capacitance	C_{IN}	$V_F = 0V, f = 1MHz$		33		pF

OUTPUT

Parameter	Symbol	Test Condition	Min	Тур.	Мах	Unit
High Level Supply Current	I _{CCH}	$I_F = 10mA, V_{CC} = 30V$ $V_O = Open$		1.7	3	mA
Low Level Supply Current	I _{CCL}	$I_F = 0mA, V_{CC} = 30V$ $V_O = Open$		2.0	3	mA
High Level Output Current	I _{OH}	$V_{O} = V_{CC} - 1.5V$ Pulse Width = 50µs			-1.0	А
		$V_0 = V_{CC} - 4.0V$ Pulse Width = 10µs			-3.0	А
Low Level Output Current	I _{OL}	$V_O = V_{EE} + 1.5V$ Pulse Width = 50µs	1.0			А
		$V_O = V_{EE} + 4V$ Pulse Width = 10µs	3.0			А
High Level Output Voltage	V _{OH}	$I_F = 10mA, I_O = -100mA$	V _{CC} -0.3	V _{CC} -0.1		V
Low Level Output Voltage	V _{OL}	$I_F = 0mA, I_O = 100mA$		V _{EE} + 0.1	$V_{EE}\!+\!0.25$	V
UVLO Threshold	V _{UVLO+}	$V_{O} > 5V, I_{F} = 10mA$	11.0	12.7	13.5	V
	V _{UVLO-}	$V_0 < 5V, I_F = 10mA$	9.5	11.2	12.0	V
UVLO Hysteresis	UVLO _{HYS}			1.5		V



ELECTRICAL CHARACTERISTICS (Typical Values at $V_{cc} - V_{EE} = 30V$ and $T_A = 25^{\circ}C$, Minimum and Maximum Values at Recommended Operating Conditions, unless otherwise specified)

SWITCHING

Parameter	Symbol	Test Condition	Min	Тур.	Мах	Unit
Propagation Delay Time to High Output Level	t _{PLH}	$I_F = 8 \text{ to } 16\text{mA}$ $V_{CC} = 15 \text{ to } 30\text{V}$ $V_{EE} = 0\text{V}$	50		200	ns
Propagation Delay Time to Low Output Level	t _{PHL}	$Rg = 10\Omega$ Cg = 10nF f = 10kHz	50		200	
Pulse Width Distortion $ t_{PHL} - t_{PLH} $ for any given Device	PWD	Duty Cycle = 50%		10	70	
Propagation Delay Difference between any two Devices	PDD		-100		100	
Output Rise Time (10% to 90%)	t _r			35		
Output Fall Time (90% to 10%)	t _f			35		
Common Mode Transient Immunity at High Output Level	CM _H	$I_{F} = 10 \text{ to } 16\text{mA} \\ V_{CC} = 30\text{V} \\ V_{CM} = 1500\text{V} \\ T_{A} = 25^{\circ}\text{C}$	35	50		kV/μs
Common Mode Transient Immunity at Low Output Level	CM _L	$V_{F} = 0V$ $V_{CC} = 30V$ $V_{CM} = 1500V$ $T_{A} = 25^{\circ}C$	35	50		kV/μs

Notes :

- 1. A 0.1uF bypass capacitor must be connected across pin 6 and pin 4.
- 2. PDD is the difference between t_{PHL} and t_{PLH} between any two devices under same test conditions.
- 3. CM_H, Common Mode Transient Immunity in High stage is the maximum tolerable positive dV_{CM}/dt on the leading edge of the common mode impulse signal, V_{CM} , to assure that the output will remain high ($V_0 > 15V$).
- 4. CM_L , Common Mode Transient Immunity in Low stage is the maximum tolerable negative dV_{CM}/dt on the trailing edge of the common mode impulse signal, V_{CM} , to assure that the output will remain low $(V_0 < 1V)$.



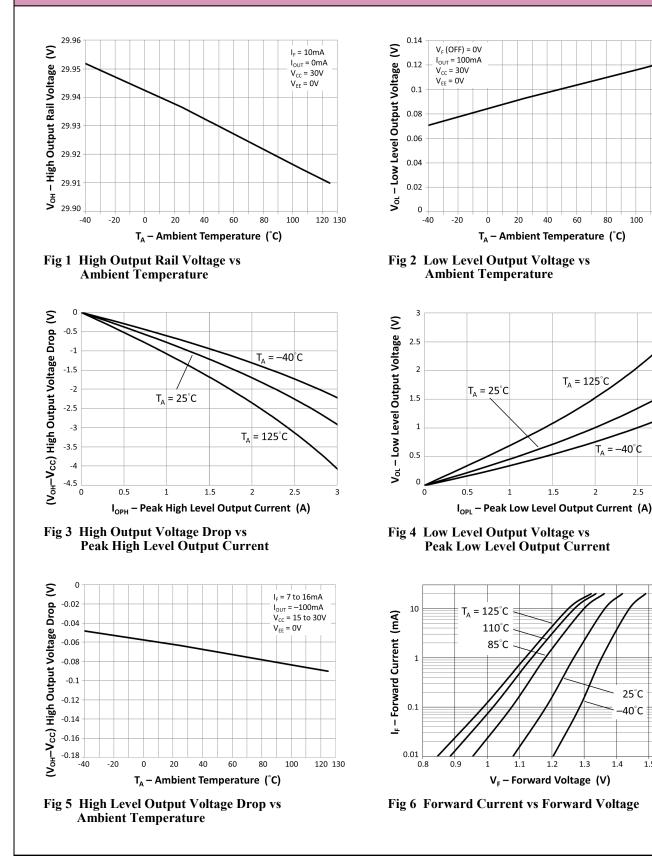
ELECTRICAL CHARACTERISTICS (Typical Values at $V_{CC} - V_{EE} = 10V$ to 30V and $T_A = 25^{\circ}C$, Minimum and Maximum Values at Recommended Operating Conditions, unless otherwise specified)

ISOLATION (Typical Values at $T_A = 25^{\circ}C$)

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Insulation Voltage	V _{ISO}	$\begin{array}{l} RH \leq 40\% \text{ to } 60\% \\ t=1 \text{ min, } T_A = 25^\circ C \end{array}$	5000			V
Input - Output Resistance	R _{I-O}	$V_{I-O} = 500 VDC$		10 ¹²		Ω
Input - Output Capacitance	C _{I-O}	$f = 1MHz, T_A = 25^{\circ}C$		0.92		pF

Device is considered a two terminal device: pins 1, 2, 3 are shorted together and pins 4, 5, 6 are shorted together.





1.6

120 130

100

2.5

25°C

-40°C

1.4

1.5

3



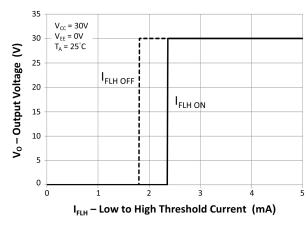


Fig 7 I_{FLH} Hysteresis

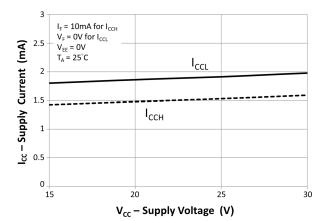
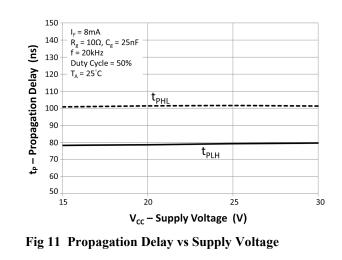


Fig 9 Supply Current vs Supply Voltage



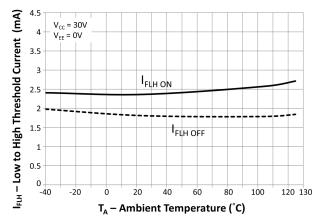


Fig 8 I_{FLH} vs Ambient Temperature

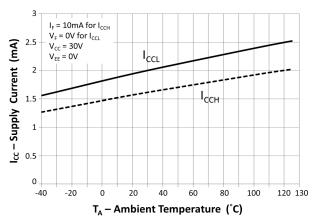


Fig 10 Supply Current vs Ambient Temperature

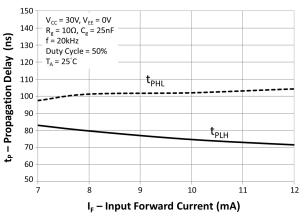
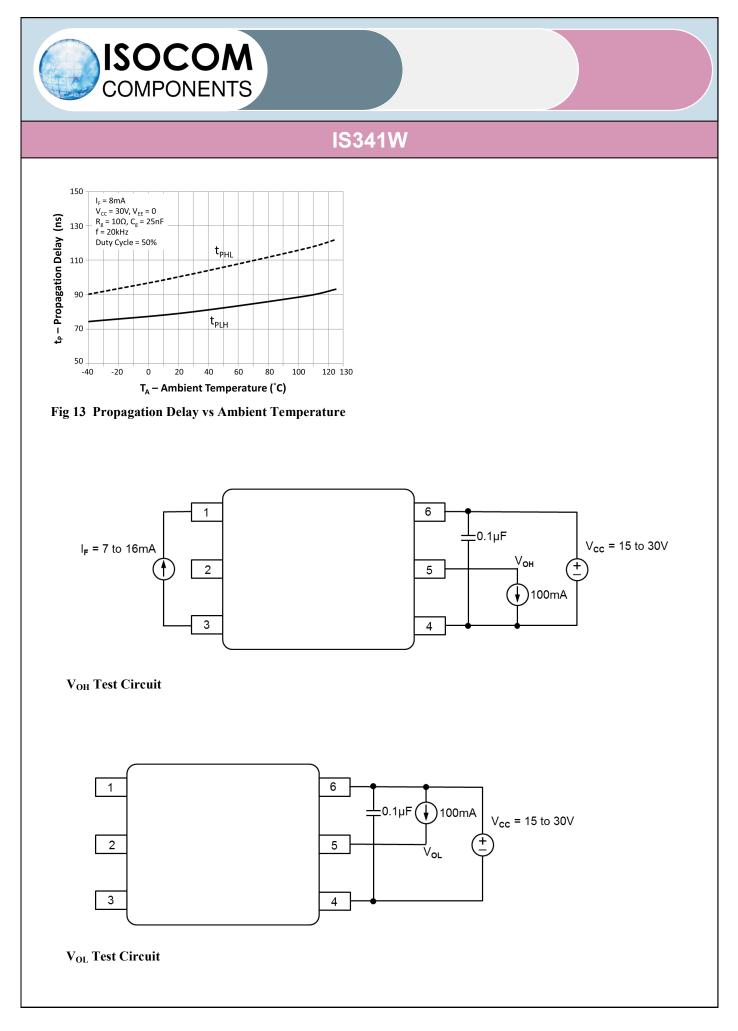
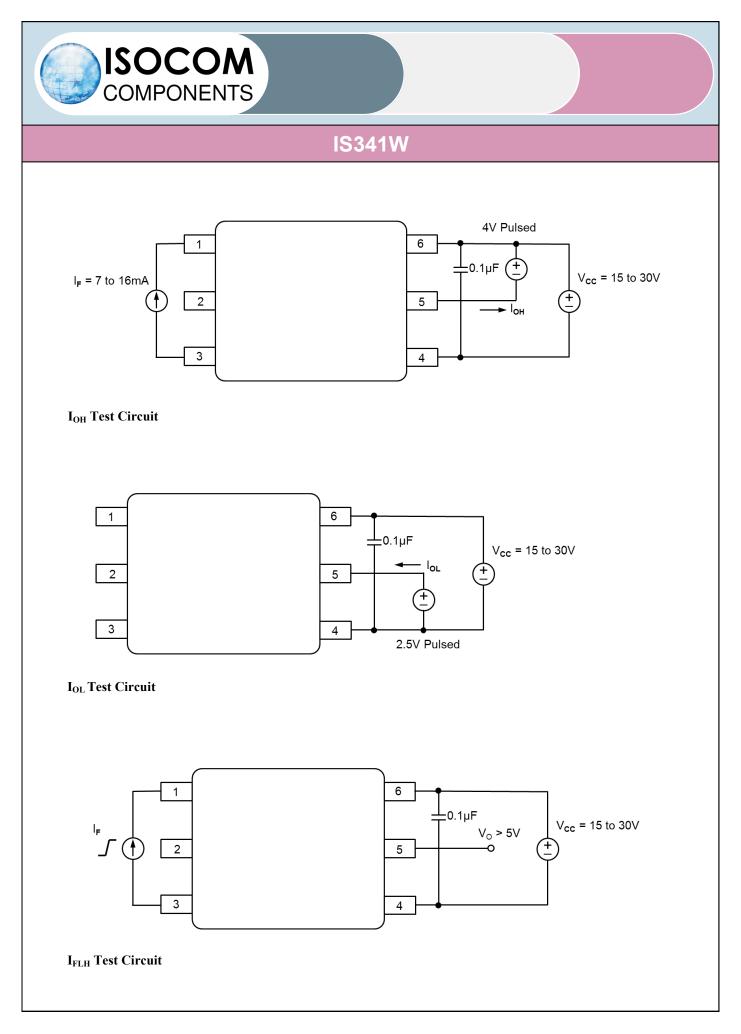
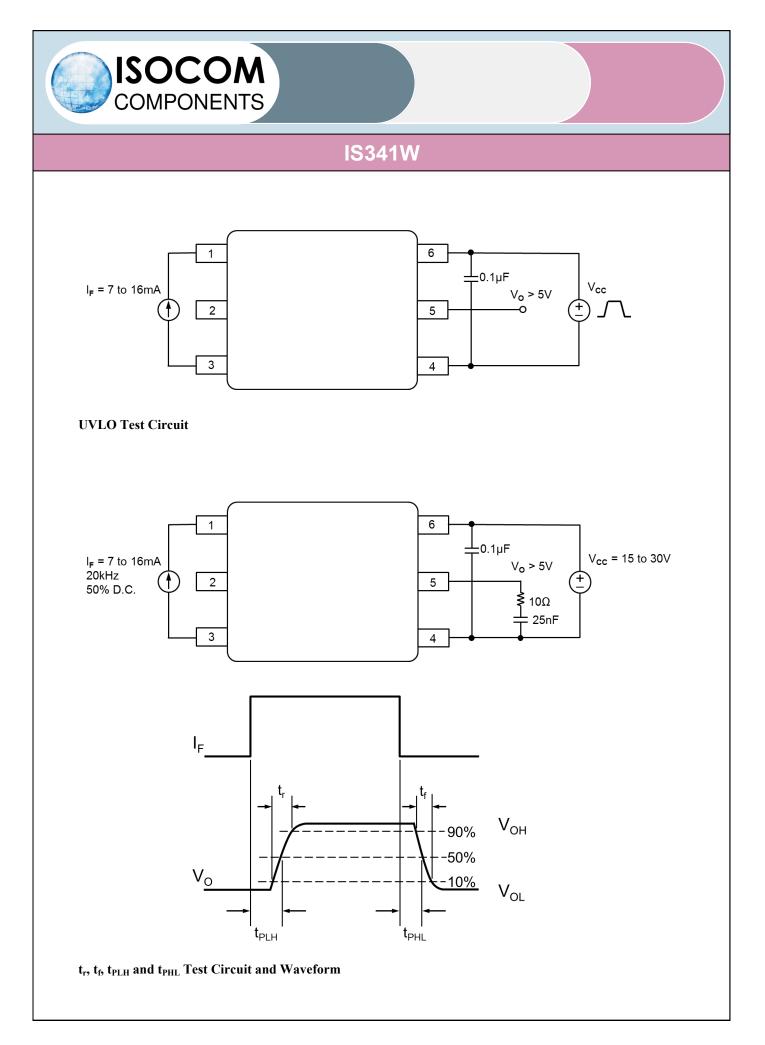
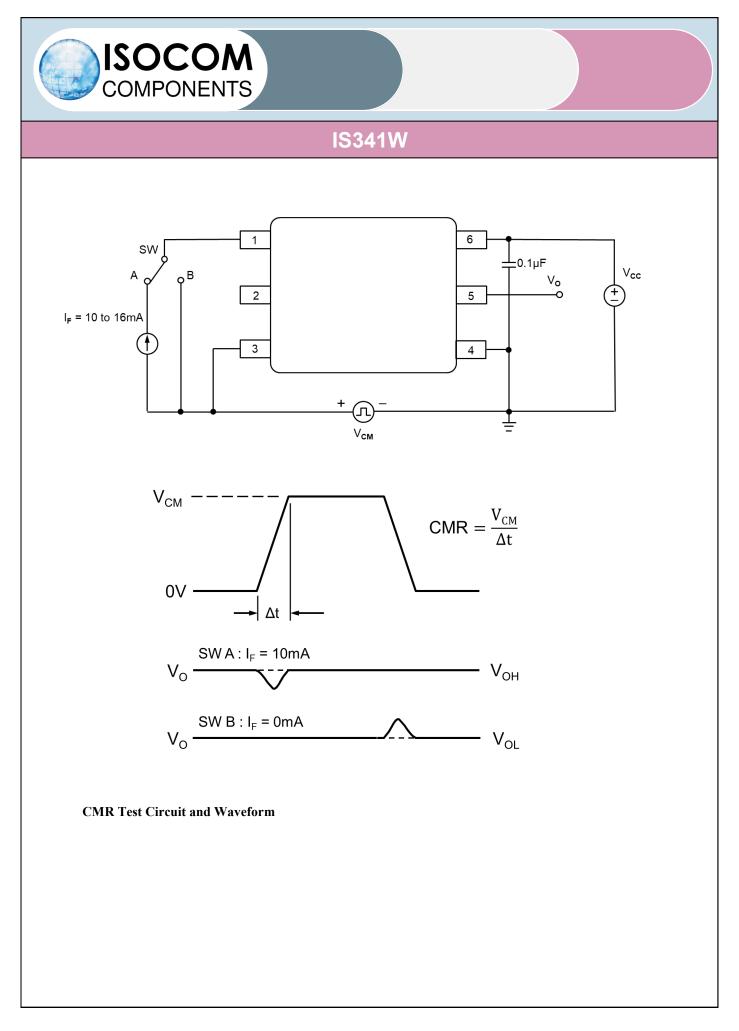


Fig 12 Propagation Delay vs Forward Current







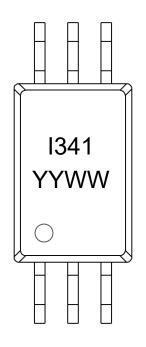




ORDER INFORMATION

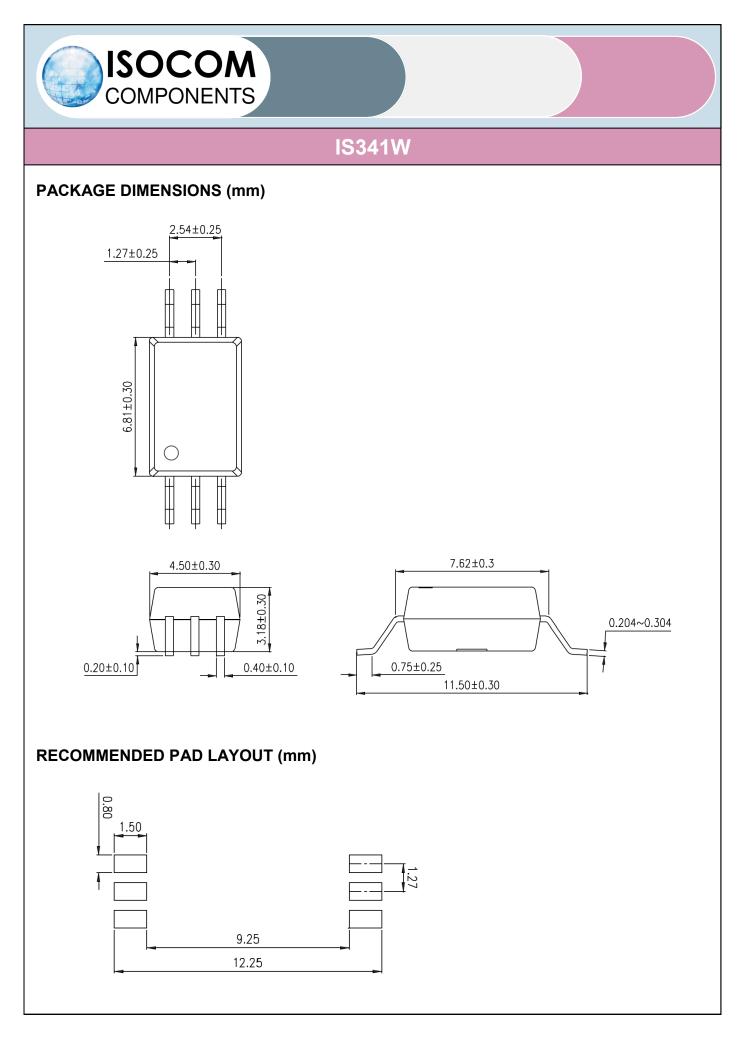
	IS341W					
After PN	PN	Description	Packing quantity			
None	IS341W	Stretched SO6 Wide Lead Separation	1000 pcs per reel			

DEVICE MARKING



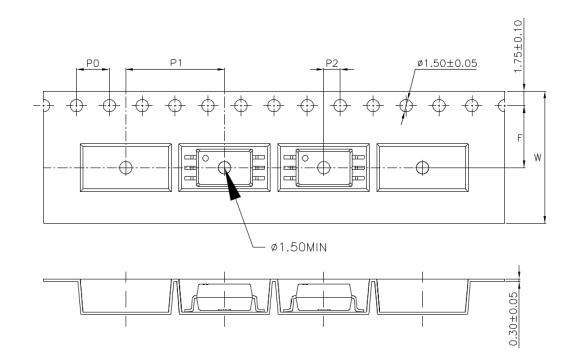
1341	denotes Device Part Number

- YY denotes 2 digit Year code
- WW denotes 2 digit Week code





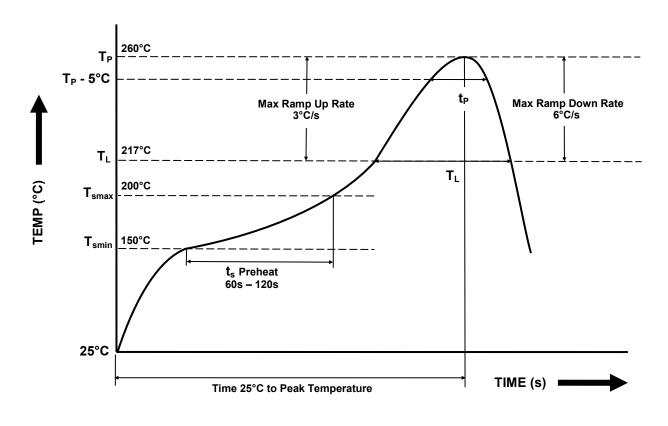
TAPE AND REEL PACKAGING



Description	Symbol	Dimension mm (inch)
Tape Width	W	16 ± 0.3 (0.63)
Pitch of Sprocket Holes	Po	4 ± 0.1 (0.16)
Distance of Compartment to Sprocket Holes	F	7.5 ± 0.1 (0.3)
Distance of Compartment to Sprocket holes	P ₂	2 ± 0.1 (0.079)
Distance of Compartment to Compartment	P ₁	16 ± 0.1 (0.63)



IR REFLOW SOLDERING TEMPERATURE PROFILE One Time Reflow Soldering is Recommended. Do not immerse device body in solder paste.



Profile Details	Conditions
Preheat - Min Temperature (T _{SMIN}) - Max Temperature (T _{SMAX}) - Time T _{SMIN} to T _{SMAX} (t _s)	150°C 200°C 60s - 120s
$\label{eq:solution} \begin{array}{l} \textbf{Soldering Zone} \\ \text{-} Peak Temperature (T_P) \\ \text{-} Time at Peak Temperature \\ \text{-} Liquidous Temperature (T_L) \\ \text{-} Time within 5^{\circ}C of Actual Peak Temperature (T_P - 5^{\circ}C) \\ \text{-} Time maintained above T_L (t_L) \\ \text{-} Ramp Up Rate (T_L to T_P) \\ \text{-} Ramp Down Rate (T_P to T_L) \end{array}$	260°C 10s max 217°C 30s max 60s - 100s 3°C/s max 6°C/s max
Average Ramp Up Rate (T _{smax} to T _P)	3°C/s max
Time 25°C to Peak Temperature	8 minutes max



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